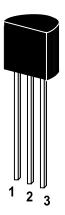
NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	100	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







Characteristics at T_{amb} =25 $^{\circ}C$

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =6V, I _C =1mA					
Current Gain Group R	h _{FE}	90	-	180	-
0	h _{FE}	135	-	270	-
Υ	h _{FE}	200	-	400	-
G	h _{FE}	300	-	600	-
Collector Base Breakdown Voltage					
at I _C =100μA	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage					
at I _C =10mA	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage					
at I _E =10μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at V _{CB} =60V	I _{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current					
at V _{EB} =5V	I _{EBO}	-	-	0.1	μΑ
Collector Saturation Voltage					
at I _C =100mA, I _B =10mA	$V_{CE(sat)}$	-	0.15	0.3	V
Base Saturation Voltage					
at I _C =100mA, I _B =10mA	$V_{BE(sat)}$	-	0.86	1	V
Gain Bandwidth Product					
at V _{CE} =6V, I _C =10mA	f_T	-	250	-	MHz
Output Capacitance					
at V _{CB} =6V, f=1MHz	C_OB		3	-	pF





